

In the Claims:

Please amend claims 1, 3, 5, 8-11 and 24 as follows:

Claim 1 (currently amended) A slurry used in a chemical mechanical polishing (CMP) process on a ruthenium thin film or a ruthenium alloy thin film, the slurry comprising:

an oxidant consisting essentially of ceric ammonium nitrate $[(\text{NH}_4)_2\text{Ce}(\text{NO}_3)_6]$

an abrasive consisting essentially of inorganic particles, ~~and~~

an acid selected from the group consisting of HNO_3 , H_2SO_4 , HCl , H_3PO_4 , and mixtures thereof, and

wherein the slurry is free of corrosion inhibitors.

Claim 2 (previously canceled)

Claim 3 (currently amended) The slurry according to claim 1, wherein the ceric ammonium nitrate is present in an amount ranging from ~~about~~ 1 to ~~about~~ 10% by weight of the slurry.

Claim 4 (previously canceled)

Claim 5 (currently amended) The slurry according to claim ~~2~~ 1, wherein the acid is HNO_3 and is present in an amount ranging from ~~about~~ 1 to ~~about~~ 10% by weight of the slurry.

Claim 6 (previously amended) The slurry according to claim 1, wherein the inorganic particles of the abrasive are selected from the group consisting of CeO_2 particles, ZrO_2 particles, Al_2O_3 particles and mixtures thereof.

Claim 7 (previously amended) The slurry according to claim 1, wherein a grain size of the abrasive is less than 1 μm .

Claim 8 (currently amended) The slurry according to claim 1, wherein the abrasive is used in an amount ranging from ~~about~~ 1 to ~~about~~ 5% by weight of the slurry.

Claim 9 (currently amended) The slurry according to claim 2 1, wherein a pH of the composition ranges from ~~about~~ 1 to ~~about~~ 7.

Claim 10 (currently amended) The slurry according to claim 2 1, wherein the pH of the composition ranges from ~~about~~ 1 to ~~about~~ 3.

Claim 11 (currently amended) The slurry according to claim 2 1, further comprising a buffer.

Claim 12 (original) The slurry according to claim 11, wherein the buffer comprises a mixed solution of approximately equal molar amounts of an organic acid and an organic acid salt.

Claim 13 (original) The slurry according to claim 12, wherein the buffer comprises a mixed solution of acetic acid and acetic acid salt.

Claims 14-23 (previously canceled)

Claim 24 (currently amended) A slurry used in a chemical mechanical polishing (CMP) process on a ruthenium thin film or a ruthenium alloy thin film that is not a ruthenium titanium nitride (RTN) thin film, the slurry comprising:

a single oxidant consisting essentially of ceric ammonium nitrate $[(\text{NH}_4)_2\text{Ce}(\text{NO}_3)_6]_1$

an abrasive consisting essentially of inorganic particles , and wherein the slurry is free of corrosion inhibitors.